

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	15 X 10 MILS
Die Thickness	8 MILS
Base Bonding Pad Area	3.6 X 2.4 MILS
Emitter Bonding Pad Area	3.6 X 2.4 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 15,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

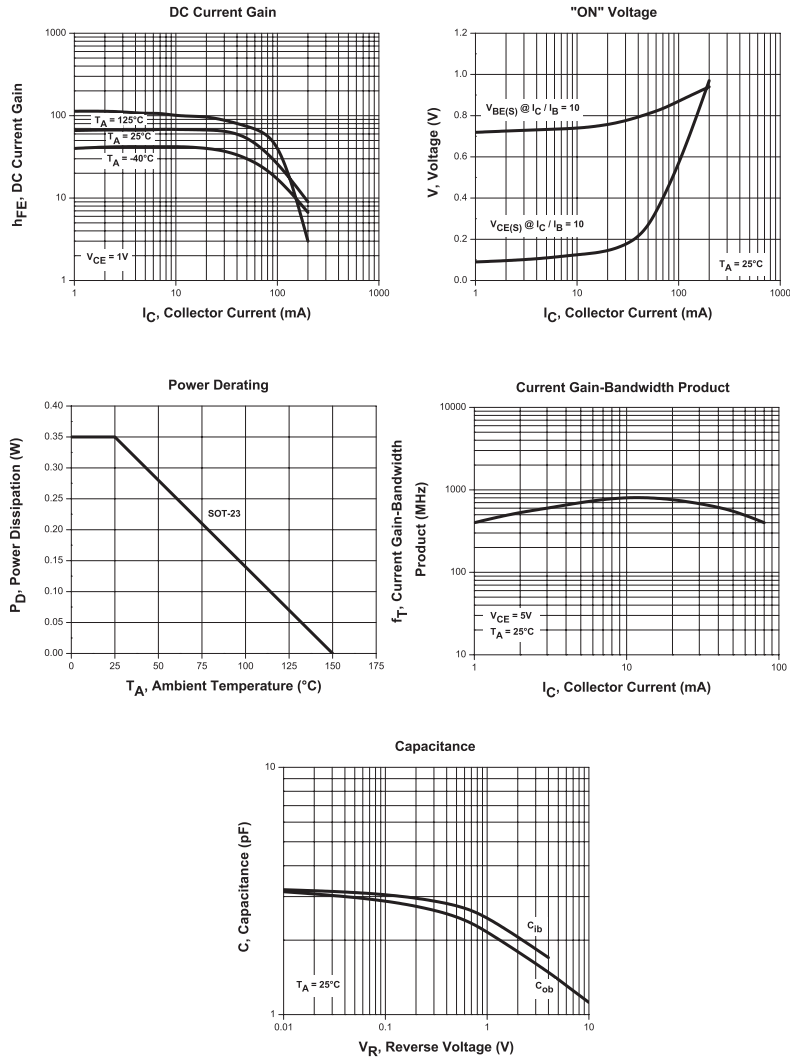
75,330

PRINCIPAL DEVICE TYPES

CMPT3640
CMPT4209
2N4209

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